

NTTFS5C453NL

Power MOSFET

40 V, 3 mΩ, 107 A, Single N-Channel

Features

- Small Footprint (3.3x3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	40	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current R _{θJC} (Notes 1, 3)	Steady State	T _C = 25°C	I _D	107	A
		T _C = 100°C		75	
Power Dissipation R _{θJC} (Note 1)		T _C = 25°C	P _D	68	W
		T _C = 100°C		34	
Continuous Drain Current R _{θJA} (Notes 1, 2, 3)	Steady State	T _A = 25°C	I _D	23	A
		T _A = 100°C		16	
Power Dissipation R _{θJA} (Notes 1 & 2)		T _A = 25°C	P _D	3.3	W
		T _A = 100°C		1.6	
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs		I _{DM}	740	A
Operating Junction and Storage Temperature			T _J , T _{stg}	−55 to +175	°C
Source Current (Body Diode)			I _S	76	A
Single Pulse Drain-to-Source Avalanche Energy (I _{L(pk)} = 7 A)			E _{AS}	215	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	2.2	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	46	

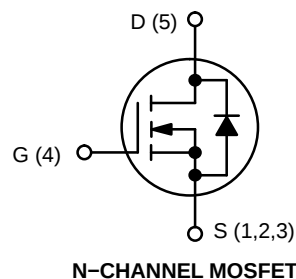
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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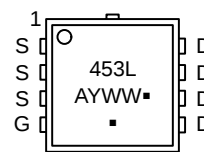
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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	3 mΩ @ 10 V	107 A
	4.8 mΩ @ 4.5 V	



WDFN8
(μ8FL)
CASE 511AB

MARKING DIAGRAM



453L = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NTTFS5C453NL

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			1.6		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 63\text{ }\mu\text{A}$	1.2		2.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-5.3		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		2.5	3	$\text{m}\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 40\text{ A}$		3.8	4.8	
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 40\text{ A}$		120		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 25\text{ V}$		2100		pF
Output Capacitance	C_{OSS}			1000		
Reverse Transfer Capacitance	C_{RSS}			42		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}; I_D = 40\text{ A}$		35		nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}; I_D = 40\text{ A}$		16		
Threshold Gate Charge	$Q_{G(TH)}$			4.0		
Gate-to-Source Charge	Q_{GS}			7.0		
Gate-to-Drain Charge	Q_{GD}			5.0		
Plateau Voltage	V_{GP}			3.2		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}, I_D = 40\text{ A}, R_G = 2.5\text{ }\Omega$		11		ns
Rise Time	t_r			110		
Turn-Off Delay Time	$t_{d(OFF)}$			21		
Fall Time	t_f			5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 40\text{ A}$	$T_J = 25^{\circ}\text{C}$		0.84	1.2	V
			$T_J = 125^{\circ}\text{C}$		0.72		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 40\text{ A}$			41		ns
Charge Time	t_a				19		
Discharge Time	t_b				22		
Reverse Recovery Charge	Q_{RR}				30		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

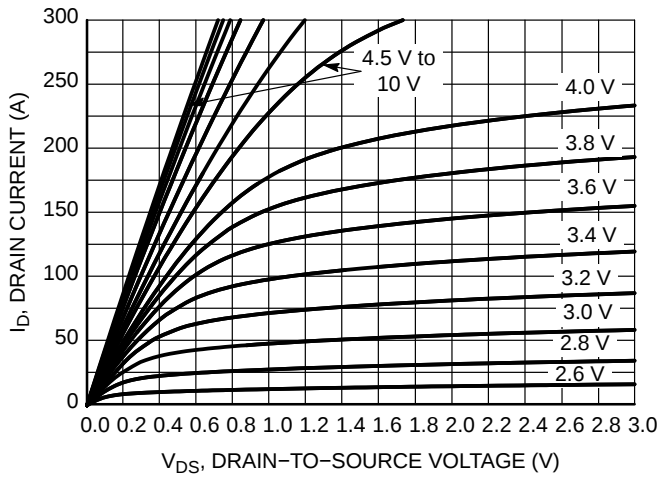


Figure 1. On-Region Characteristics

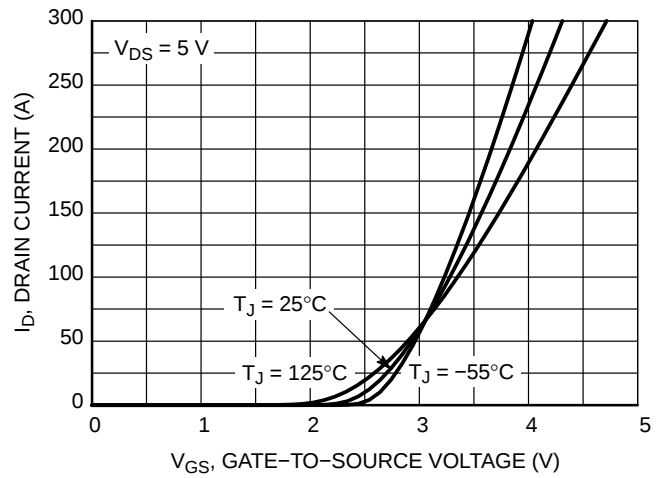


Figure 2. Transfer Characteristics

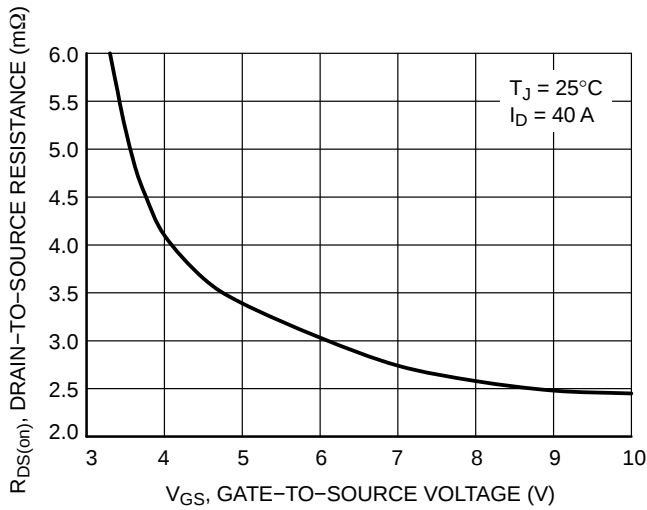


Figure 3. On-Resistance vs. Gate-to-Source Voltage

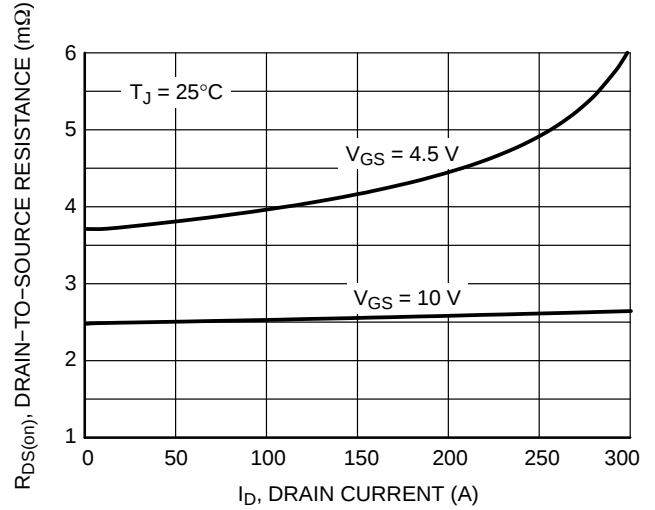


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

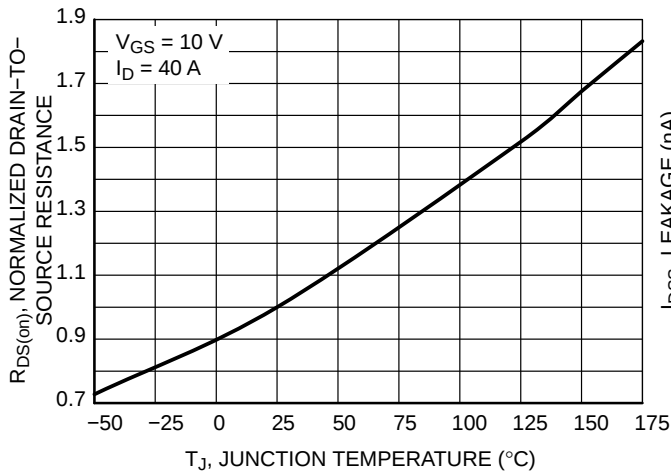


Figure 5. On-Resistance Variation with Temperature

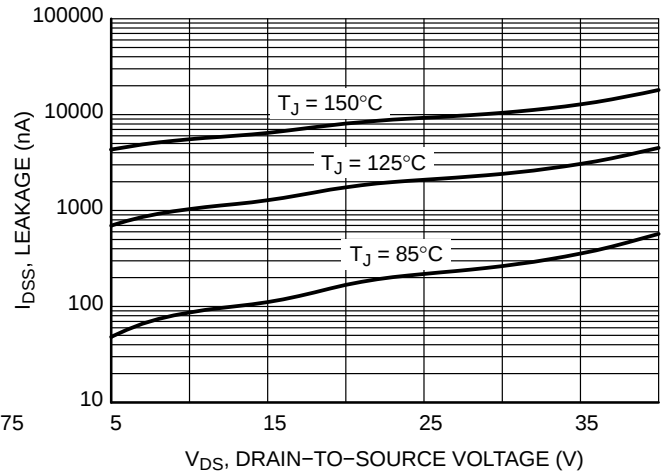


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

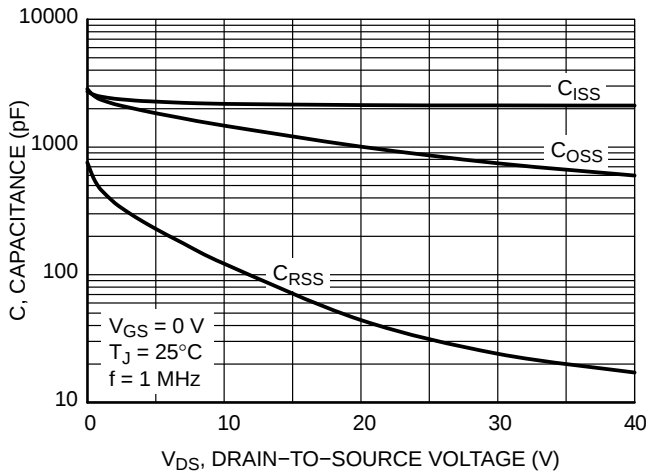


Figure 7. Capacitance Variation

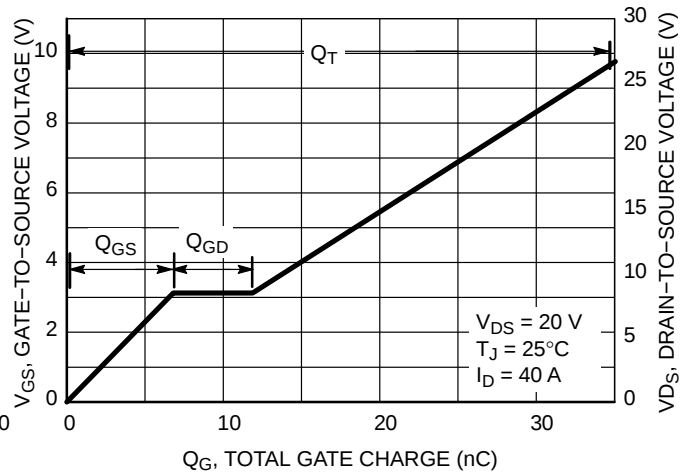


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

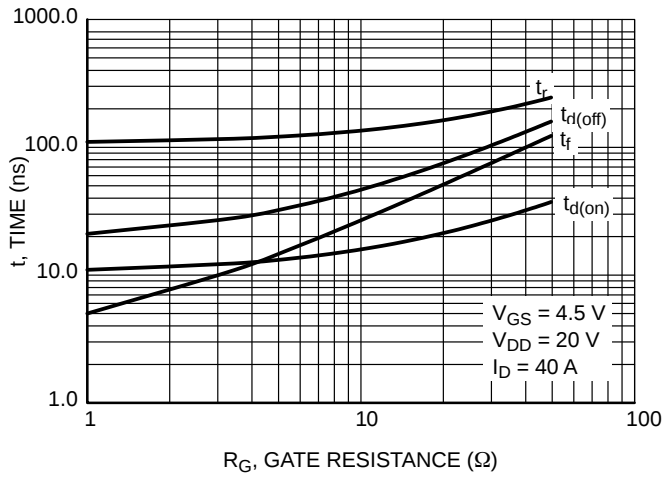


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

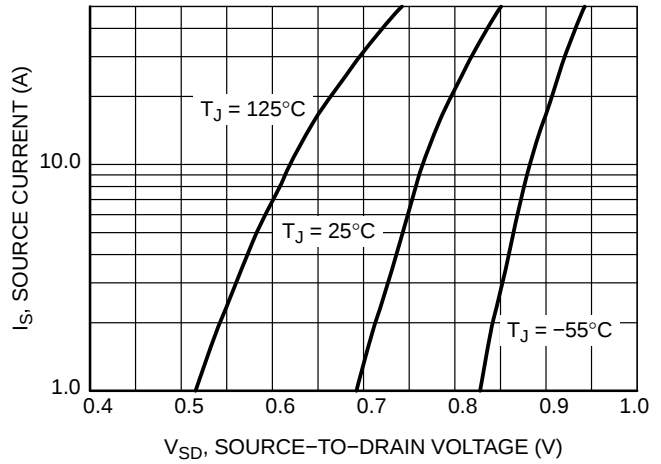


Figure 10. Diode Forward Voltage vs. Current

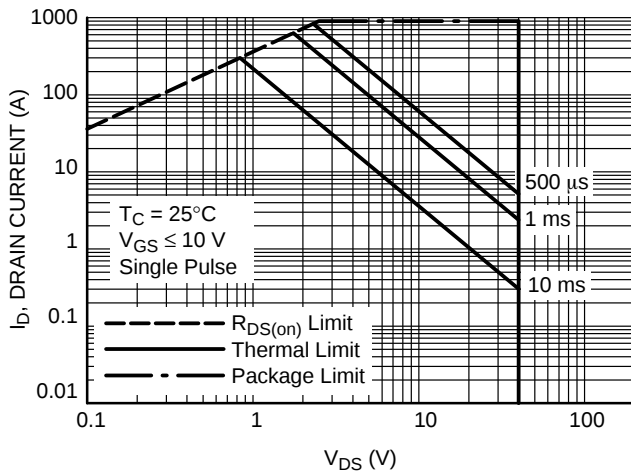


Figure 11. Safe Operating Area

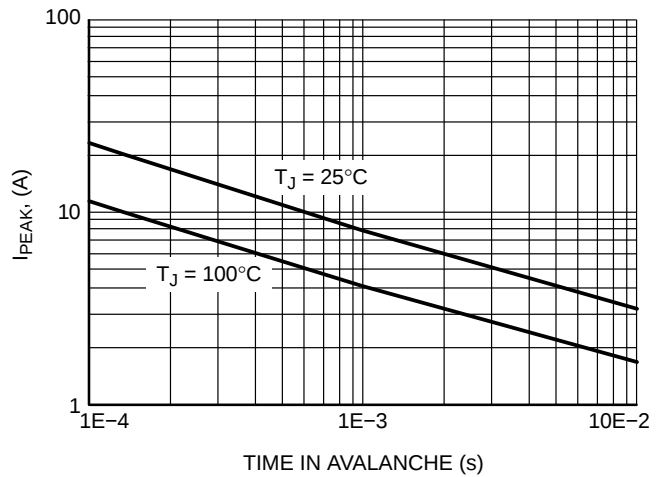


Figure 12. I_{PEAK} vs. Time in Avalanche

NTTFS5C453NL

TYPICAL CHARACTERISTICS

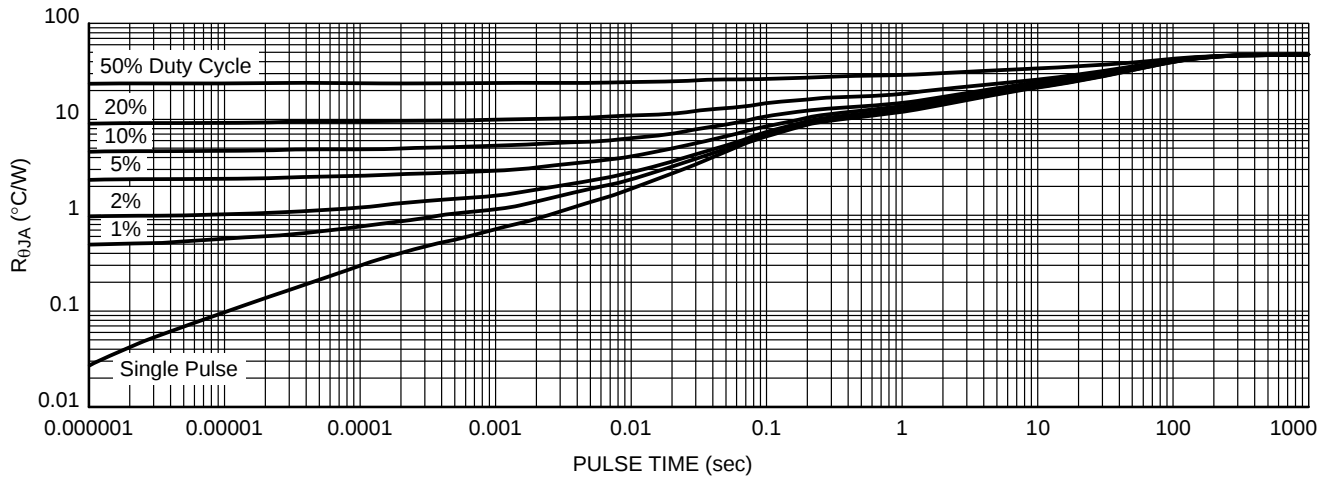


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTTFS5C453NLTAG	453L	WDFN8 (Pb-Free)	1500 / Tape & Reel
NTTFS5C453NLTWG	453L	WDFN8 (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
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- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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